

Ran Yu

List of Publications by Year in descending order

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Version: 2024-02-01

30
papers

1,189
citations

516710

16
h-index

580821

25
g-index

31
all docs

31
docs citations

31
times ranked

859
citing authors

#	ARTICLE	IF	CITATIONS
1	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
2	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
3	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
4	Improvement of carrier ballisticity in junctionless nanowire transistors. Applied Physics Letters, 2011, 98, .	3.3	43
5	Bipolar effects in unipolar junctionless transistors. Applied Physics Letters, 2012, 101, 093507.	3.3	39
6	Optimized Laser Thermal Annealing on Germanium for High Dopant Activation and Low Leakage Current. IEEE Transactions on Electron Devices, 2014, 61, 4047-4055.	3.0	39
7	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
8	Junctionless Nanowire Transistor: Complementary Metal-Oxide-Semiconductor Without Junctions. Science of Advanced Materials, 2011, 3, 477-482.	0.7	36
9	Device Design and Estimated Performance for p-Type Junctionless Transistors on Bulk Germanium Substrates. IEEE Transactions on Electron Devices, 2012, 59, 2308-2313.	3.0	31
10	A Simulation Comparison between Junctionless and Inversion-Mode MuGFETs. ECS Transactions, 2011, 35, 63-72.	0.5	29
11	Influence of channel material properties on performance of nanowire transistors. Journal of Applied Physics, 2012, 111, .	2.5	24
12	Atomically Flat Low-Resistive Germanide Contacts Formed by Laser Thermal Anneal. IEEE Transactions on Electron Devices, 2013, 60, 2178-2185.	3.0	22
13	Effect of intravalley acoustic phonon scattering on quantum transport in multigate silicon nanowire metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 034510.	2.5	19
14	Access resistance reduction in Ge nanowires and substrates based on non-destructive gas-source dopant in-diffusion. Journal of Materials Chemistry C, 2014, 2, 9248-9257.	5.5	18
15	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17
16	Resistive substrate interface tailoring for generating high-density arrays of Ge and Bi ₂ Se ₃ nanowires by electron beam lithography. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	1.2	17
17	Emission and absorption of optical phonons in Multigate Silicon Nanowire MOSFETs. Journal of Computational Electronics, 2012, 11, 249-265.	2.5	16
18	Junctionless nanowire transistor fabricated with high mobility Ge channel. Physica Status Solidi - Rapid Research Letters, 2014, 8, 65-68.	2.4	16

#	ARTICLE	IF	CITATIONS
19	Influence of discrete dopant on quantum transport in silicon nanowire transistors. Solid-State Electronics, 2012, 70, 92-100.	1.4	15
20	Fully CMOS-compatible top-down fabrication of sub-50nm silicon nanowire sensing devices. Microelectronic Engineering, 2014, 118, 47-53.	2.4	14
21	Detection of ultra-low protein concentrations with the simplest possible field effect transistor. Nanotechnology, 2019, 30, 324001.	2.6	12
22	Nanowire to Single-Electron Transistor Transition in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 26-32.	3.0	9
23	Influence of Elastic and Inelastic Electron-Phonon Interaction on Quantum Transport in Multigate Silicon Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 1029-1037.	3.0	9
24	Fabrication of Germanium-on-Insulator by low temperature direct wafer bonding. , 2010, , .		6
25	Characterization of a junctionless diode. Applied Physics Letters, 2011, 99, 013502.	3.3	6
26	Intrinsic gate delay and energy-delay product in junctionless nanowire transistors. , 2012, , .		6
27	Dissipative transport in Multigate silicon nanowire transistors. , 2010, , .		4
28	Functionalized 3D 7#x00D7;20-array of vertically stacked SiNW FET for streptavidin sensing. , 2013, , .		2
29	Component design and testing for a miniaturised autonomous sensor based on a nanowire materials platform. Microsystem Technologies, 2014, 20, 971-988.	2.0	1
30	Electron transport in germanium junctionless nanowire transistors. , 2012, , .		0